2024년 1월 25일(목), 09:00-10:45
Room C(103),1층

J. Nano-Science & Technology 분과

[TC1-J] van der Waals Heterostructure Electronics

좌장: 이관형 교수(서울대학교), 이명재 교수(서울대학교)

초청발표 TC1-J-1 09:00-09:30	2D Materials Design for Angstrom-scale Multi-stack Devices Hyeon-Jin Shin SAIT
TC1-J-2 09:30-09:45	NMOS Inverter based on Vertically Stacked MoS_2 n-MOSFET Using Semi-metallic $PtSe_2$ Contacts Jae Eun Seo[1], Minseung Gyeon[2], Jisoo Seok[1], Kibum Kang[2], and Jiwon Chang[1] [1]Department of System Semiconductor Engineering and Department of Materials Science and Engineering, Yonsei University, [2]Department of Materials Science and Engineering, KAIST
TC1-J-3 09:45-10:00	Atomic-Thin Dielectric Integration with Hexagonal Boron Nitride for Large Scale MoS_2 Field Effect Transistors Woo-Ju Lee[1,2], Min-Yeong Choi[1,2], Seong-Jun Yang[1], and Cheol-Joo Kim[1,2] [1]Center for Van der Waals Quantum Solids, IBS, [2]Department of Chemical Engineering, POSTECH
초청발표 TC1-J-4 10:00-10:30	Reliable Transistors Fabricated via Two-dimensional Layer Transfer Assisted Heterogeneous Integration Techniques Hyun S. Kum Yonsei University
TC1-J-5 10:30-10:45	Two-dimensional Layer Induced Resistive Switching Properties of Hafnia-Based Heterostructure Donghyeon Lee[1], Seungmo Kim[2,3], and Sanghan Lee[1] [1]School of Materials Science and Engineering, GIST, [2]Center for Semiconductor Technology Convergence, POSTECH, [3]Department of Electrical Engineering, POSTECH